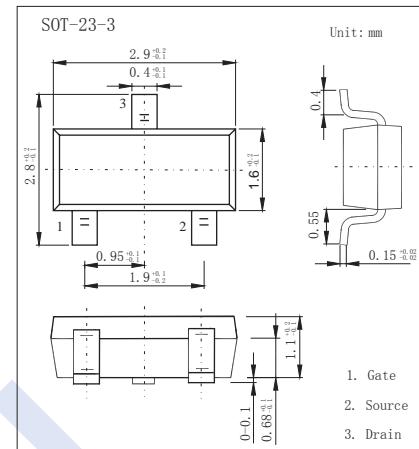
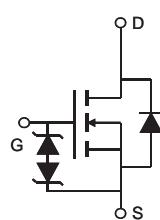


N-Channel Enhancement MOSFET

AO3416 (KO3416)

■ Features

- $V_{DS} (V) = 20V$
- $I_D = 6.5 A (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 22m\Omega (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 26m\Omega (V_{GS} = 2.5V)$
- $R_{DS(ON)} < 34m\Omega (V_{GS} = 1.8V)$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_D	6.5	A
		5.2	
Pulsed Drain Current	I_{DM}	30	
Power Dissipation	P_D	1.4	W
		0.9	
Thermal Resistance.Junction- to-Ambient Steady State	R_{thJA}	90	°C/W
		125	
Thermal Resistance.Junction-to-Foot	R_{thJF}	80	
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to 150	

N-Channel Enhancement MOSFET

AO3416 (KO3416)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	20			V
Zero Gate Voltage Drain Current	$I_{DS(0)}$	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$		1		μA
		$V_{DS}=20\text{V}, V_{GS}=0\text{V}, T_a=70^\circ\text{C}$		5		
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 8\text{V}$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250 \mu\text{A}$	0.4	0.7	1.1	V
On-State Drain Current	$I_{D(on)}$	$V_{DS}=5\text{V}, V_{GS}=4.5\text{V}$	30			A
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5\text{V}, I_D=6.5\text{A}$		16	22	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=6.5\text{A}, T_J=125^\circ\text{C}$		22	30	
		$V_{GS}=2.5\text{V}, I_D=5.5\text{A}$		18	26	
		$V_{GS}=1.8\text{V}, I_D=5\text{A}$		21	34	
Forward Transconductance	g_{FS}	$V_{DS}=5\text{V}, I_D=6.5\text{A}$		50		S
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$		1295	1650	pF
Output Capacitance	C_{oss}			160		
Reverse Transfer Capacitance	C_{rss}			87		
Gate Resistance	R_g	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		1.8		$\text{k}\Omega$
Total Gate Charge	Q_g	$V_{GS}=4.5\text{V}, V_{DS}=10\text{V}, I_D=6.5\text{A}$		10		nC
Gate Source Charge	Q_{gs}			4.2		
Gate Drain Charge	Q_{gd}			2.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=10\text{V}, V_{GEN}=4.5\text{V}$ $R_L=1.54\Omega, R_G=3\Omega$		280		ns
Turn-On Rise Time	t_r			328		
Turn-Off Delay Time	$t_{d(off)}$			3.76		
Turn-Off Fall Time	t_f			2.24		
Body Diode Reverse Recovery Time	t_{rr}	$I_F=6.5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		31	41	nC
Body Diode Reverse Recovery Charge	Q_{rr}			6.8		
Maximum Body-Diode Continuous Current	I_s				2	A
Diode Forward Voltage	V_{SD}	$I_s=1.0\text{A}, V_{GS}=0\text{V}$		0.62	1	V

*1 Pulse test: $PW \leq 300\text{us}$ duty cycle $\leq 2\%$.

■ Marking

Marking	3416
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N-Channel Enhancement MOSFET

AO3416 (KO3416)

■ Typical Characteristics

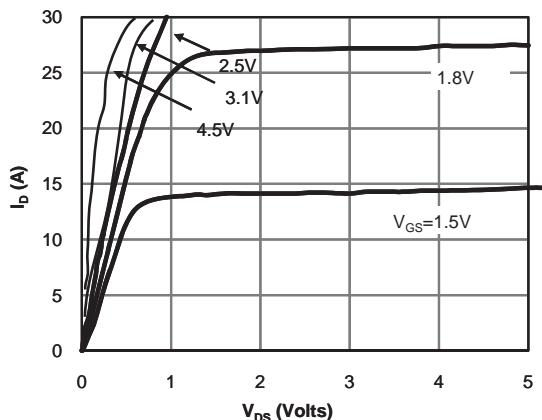


Fig 1: On-Region Characteristics (Note E)

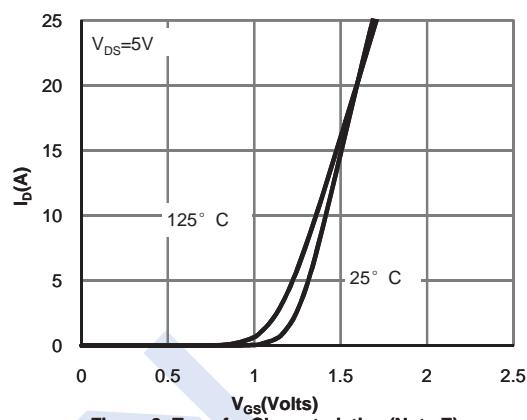


Figure 2: Transfer Characteristics (Note E)

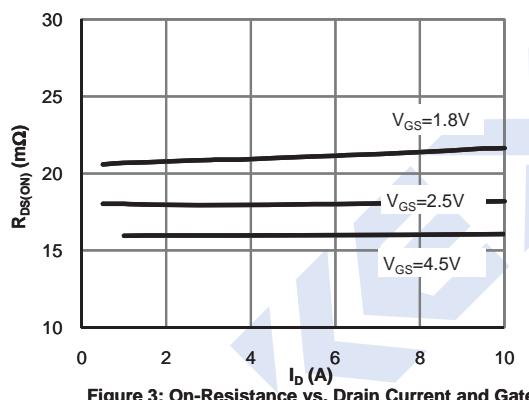


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

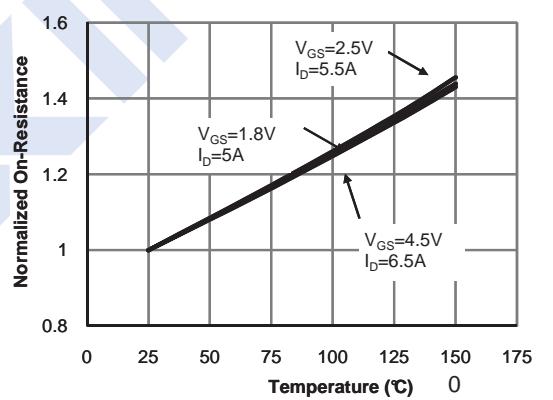


Figure 4: On-Resistance vs. Junction Temperature (Note E)

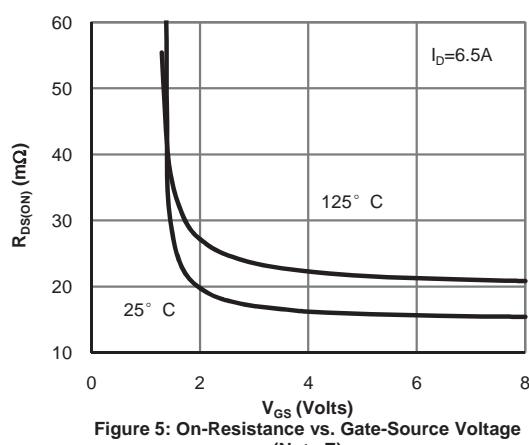


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

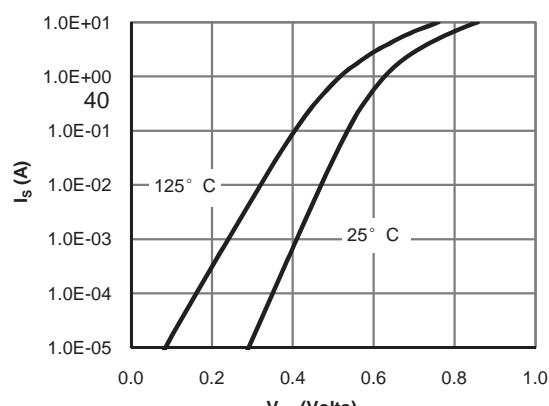


Figure 6: Body-Diode Characteristics (Note E)

N-Channel Enhancement MOSFET

AO3416 (KO3416)

■ Typical Characteristics

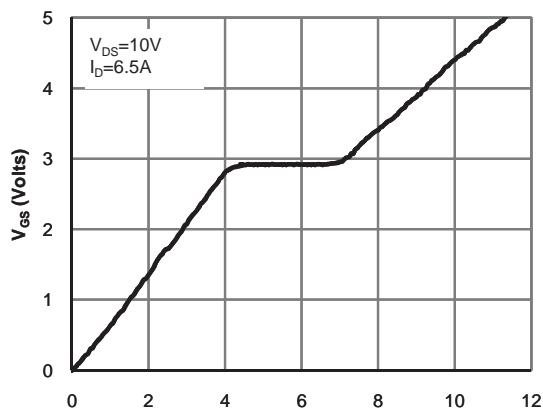


Figure 7: Gate-Charge Characteristics

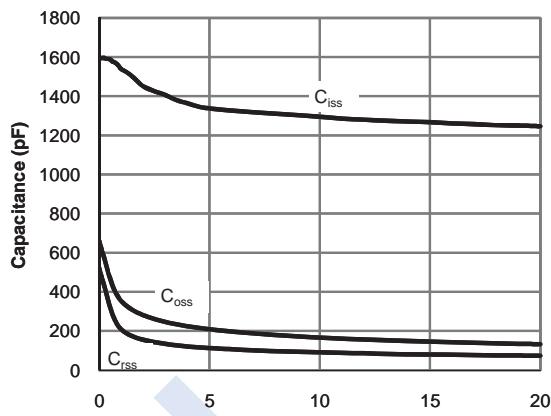


Figure 8: Capacitance Characteristics

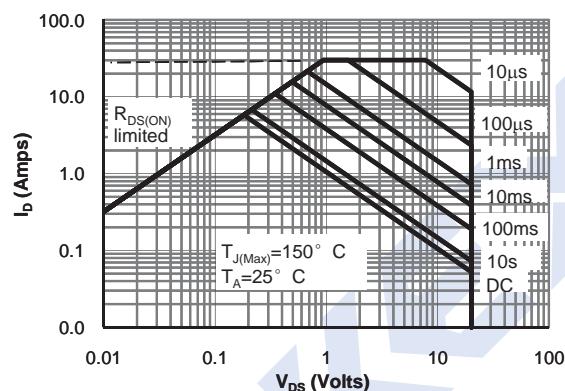


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

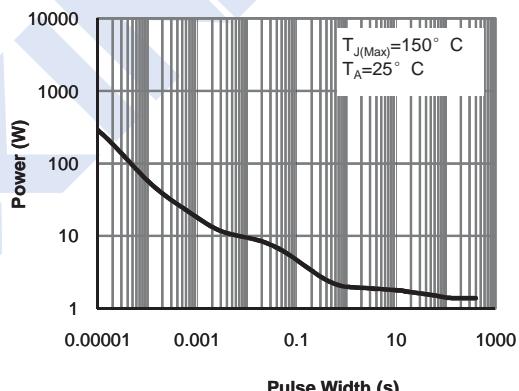


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

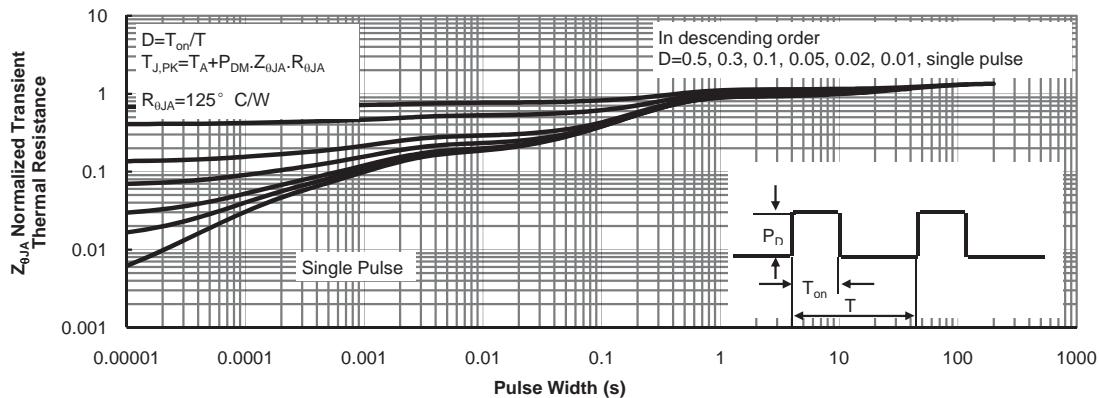


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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